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March 2009

FDS8638

N-Channel PowerTrench $^{\! \rm I\!R}$ MOSFET 40 V, 18 A, 4.3 m Ω

Features

- Max $r_{DS(on)}$ = 4.3 m Ω at V_{GS} = 10 V, I_D = 18 A
- Max $r_{DS(on)} = 5.4 \text{ m}\Omega$ at $V_{GS} = 4.5 \text{ V}$, $I_D = 16 \text{ A}$
- High performance trench technology for extremely low r_{DS(on)}
- 100% UIL Tested
- RoHS Compliant

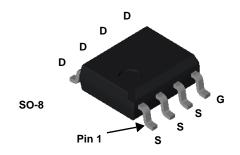


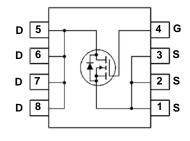
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Applications

- Synchronous Rectifier
- Load Switch





MOSFET Maximum Ratings TA = 25 °C unless otherwise noted

Symbol	Para	meter		Ratings	Units
V _{DS}	Drain to Source Voltage			40	V
V_{GS}	Gate to Source Voltage			±20	V
	Drain Current -Continuous			18	^
^I D	-Pulsed			100	Α
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	541	mJ
D	Power Dissipation	T _A = 25 °C	(Note 1a)	2.5	W
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1b)	1	VV
T _J , T _{STG}	Operating and Storage Junction Temper	erature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	°C/M
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS8638	FDS8638	SO-8	13 " 12 mm		2500 units

Electrical Characteristics $T_J = 25 \, ^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25 °C		32		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 32 V, V _{GS} = 0 V			1	μА
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1.0	1.9	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		-7		mV/°C
		V _{GS} = 10 V, I _D = 18 A		3.3	4.3	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$		4.0	5.4	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}, T_J = 125 °C$		4.8	6.3	
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 18 \text{ A}$		88		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 45.V.V 0.V	4270	5680	pF
Coss	Output Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	1175	1560	pF
C _{rss}	Reverse Transfer Capacitance	1 – 1 1011 12	120	180	рF
R_{α}	Gate Resistance		0.9		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	.,	16	30	ns
t _r	Rise Time	$V_{DD} = 20 \text{ V, } I_{D} = 18 \text{ A,}$ $V_{GS} = 10 \text{ V, } R_{GEN} = 6 \Omega$	6	13	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = 10 V, K _{GEN} = 6 12	39	63	ns
t _f	Fall Time		5	10	ns
Q_g	Total Gate Charge	V _{GS} = 0 V to 10 V	61	86	nC
Qg	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $I_{D} = 20 \text{ V},$ $I_{D} = 18 \text{ A}$	27	39	nC
Q _{gs}	Gate to Source Charge	I _D = 16 A	12		nC
Q_{gd}	Gate to Drain "Miller" Charge		7.2		nC

Drain-Source Diode Characteristics

	Veb Source to Drain Dioge Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 18 \text{ A}$	(Note 2)	0.81	1.3	V
VSD		V _{GS} = 0 V, I _S = 2.1 A	(Note 2)	0.71	1.2	V
t _{rr}	Reverse Recovery Time	I _F = 18 A, di/dt = 100 A/μs		51	82	ns
Q _{rr}	Reverse Recovery Charge	$-1F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{S}$		30	49	nC

1. R_{0LA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0LC} is guaranteed by design while R_{0CA} is determined by the user's board design.



a) 50 °C/W when mounted on a 1 in² pad of 2 oz copper.



b) 125 °C/W when mounted on a minimum pad.

- 2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%. 3. Starting T $_J$ = 25 °C, $\,$ L = 3 mH, $\,$ I $_{AS}$ = 19 A, $\,$ V $_{DD}$ = 40 V, $\,$ V $_{GS}$ = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

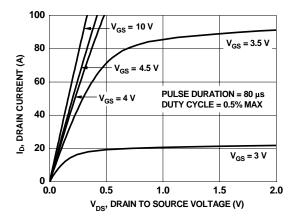


Figure 1. On Region Characteristics

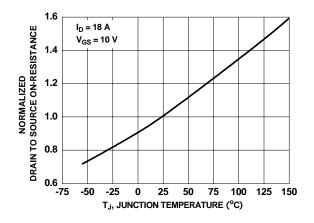


Figure 3. Normalized On Resistance vs Junction Temperature

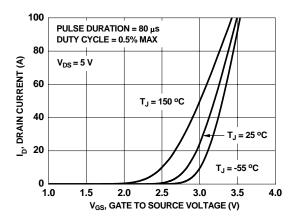


Figure 5. Transfer Characteristics

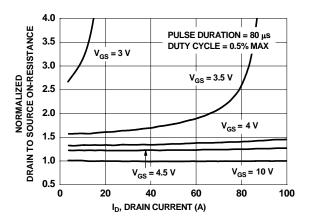


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

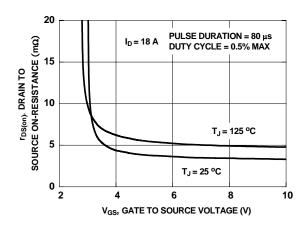


Figure 4. On-Resistance vs Gate to Source Voltage

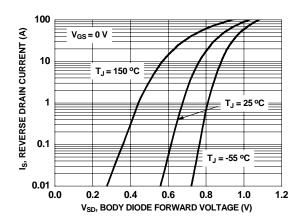


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

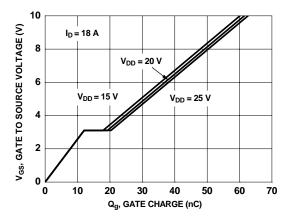


Figure 7. Gate Charge Characteristics

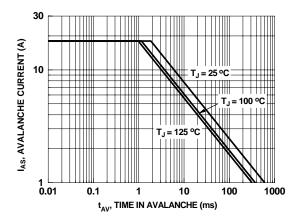


Figure 9. Unclamped Inductive Switching Capability

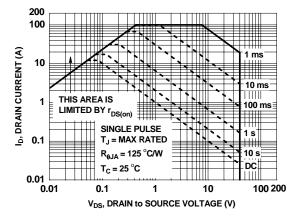


Figure 11. Forward Bias Safe Operating Area

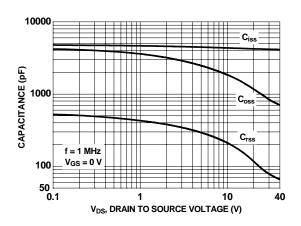


Figure 8. Capacitance vs Drain to Source Voltage

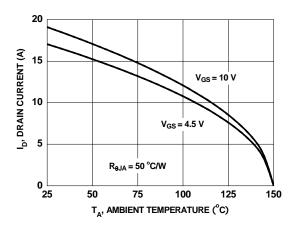


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

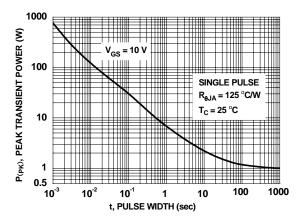


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25$ °C unless otherwise noted

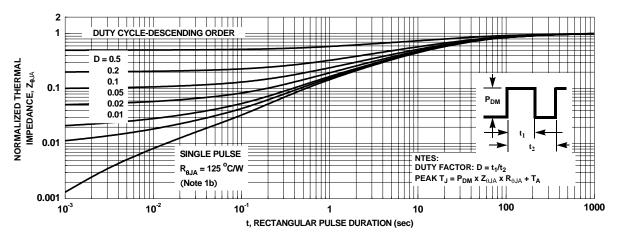


Figure 13. Junction-to-Ambient Transient Thermal Response Curve





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